

ZVP1320F

200V P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET IN SOT23

Features and Benefits

- $V_{(BR)DSS} > -200V$
- $R_{DS(on)} \leq 80\Omega @ V_{GS} = -10V$
- Maximum continuous drain current $I_D = -35mA$
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

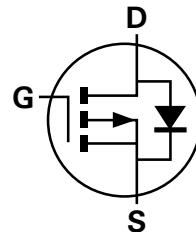
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

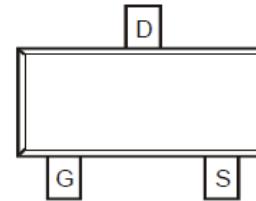
SOT23



Top View



Device symbol


Pin-Out
Top View

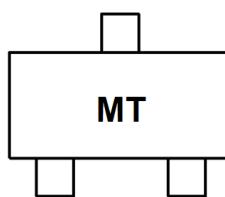
Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVP1320FTA	MT	7	8	3000

Notes:

1. No purposefully added lead
2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



MT = Product Type Marking Code

ZVP1320F

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-200	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	I_D	-35	mA
Pulsed Drain Current (Note 5)	I_{DM}	-400	mA

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

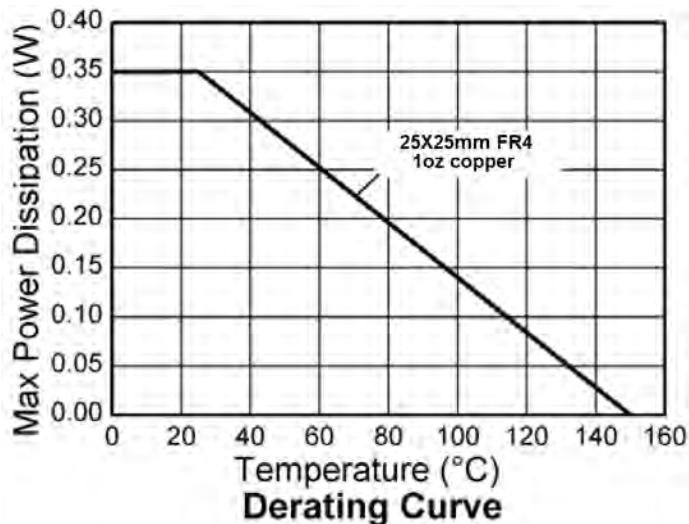
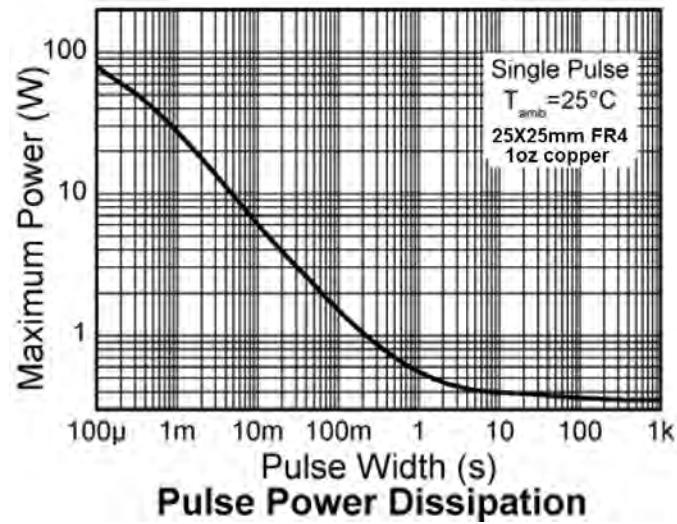
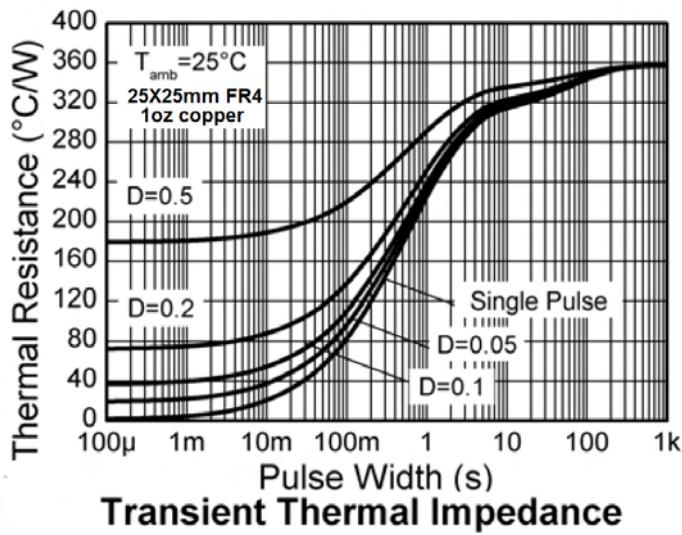
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:

- 4. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.
- 5. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.

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Thermal Characteristics



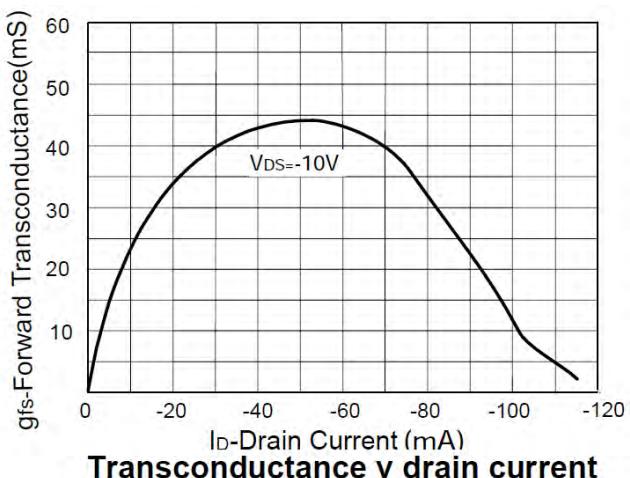
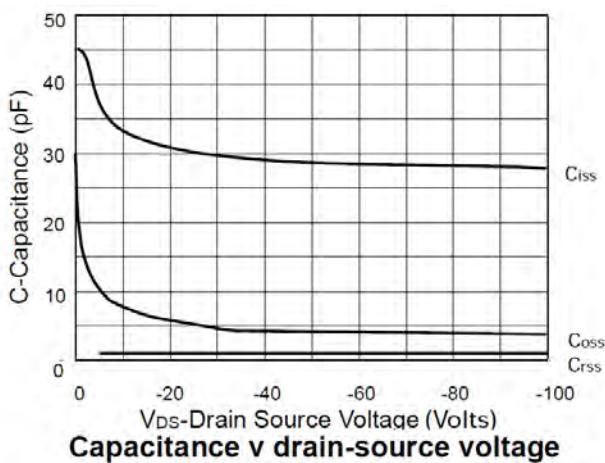
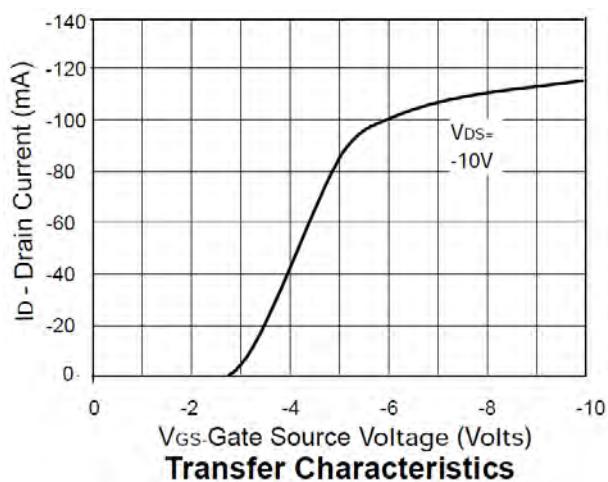
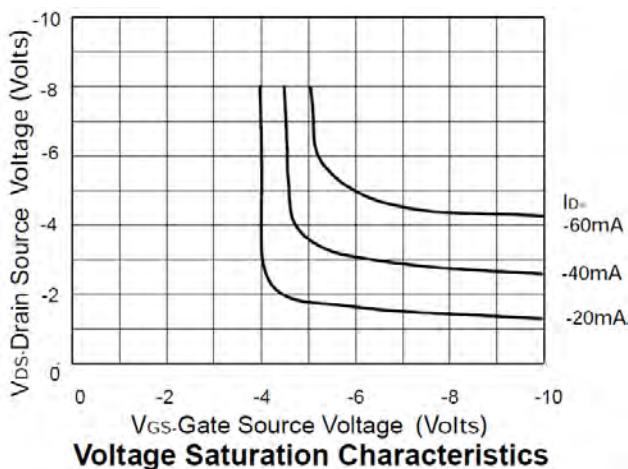
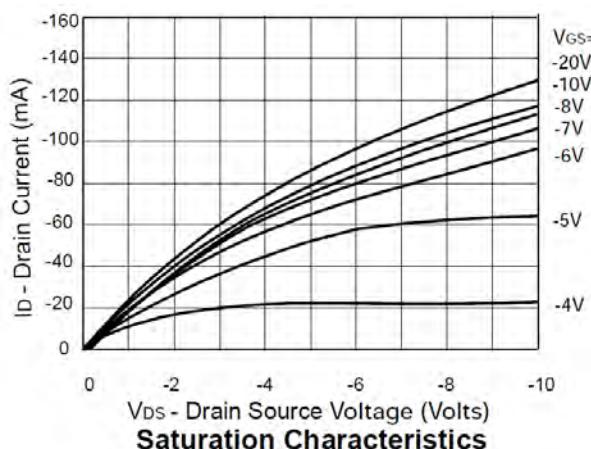
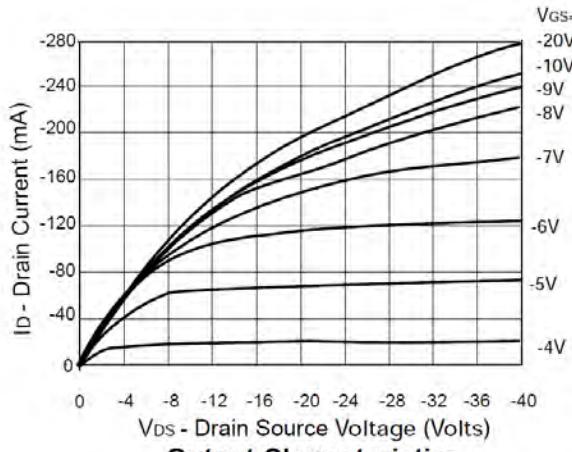
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-200	-	-	V	$V_{\text{GS}} = 0\text{V}$, $I_D = -1\text{mA}$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	-	-	-1 -20	μA	$V_{\text{DS}} = -200\text{V}$, $V_{\text{GS}} = 0\text{V}$ $V_{\text{DS}} = -160\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_A = 125^\circ\text{C}$
Gate-Source Leakage	I_{GSS}	-	-	± 20	nA	$V_{\text{GS}} = \pm 20\text{V}$, $V_{\text{DS}} = 0\text{V}$
On-State Drain Current	$I_{\text{D(on)}}$	-100	-	-	mA	$V_{\text{GS}} = -10\text{V}$, $V_{\text{DS}} = -15\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	-1.5	-	-3.5	V	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = -1\text{mA}$
Static Drain-Source On-Resistance	$R_{\text{DS(on)}}$	-	-	80	Ω	$V_{\text{GS}} = -10\text{V}$, $I_D = -50\text{mA}$
Forward Transconductance	g_{fs}	25	-	-	mS	$V_{\text{DS}} = -15\text{V}$, $I_D = -50\text{mA}$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	-	50	pF	$V_{\text{DS}} = -25\text{V}$, $V_{\text{GS}} = 0\text{V}$, $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	-	15	pF	
Reverse Transfer Capacitance	C_{rss}	-	-	5	pF	
Turn-On Delay Time	$t_{\text{D(on)}}$	-	-	8	ns	
Turn-On Rise Time	t_r	-	-	8	ns	$V_{\text{DS}} = -25\text{V}$, $I_D = -50\text{mA}$
Turn-Off Delay Time	$t_{\text{D(off)}}$	-	-	8	ns	
Turn-Off Fall Time	t_f	-	-	16	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.

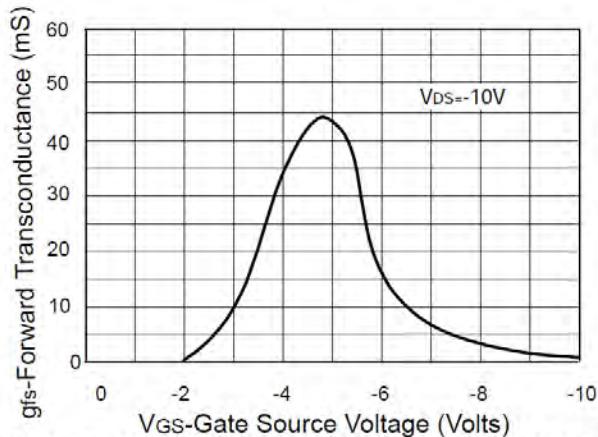
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Electrical Characteristics

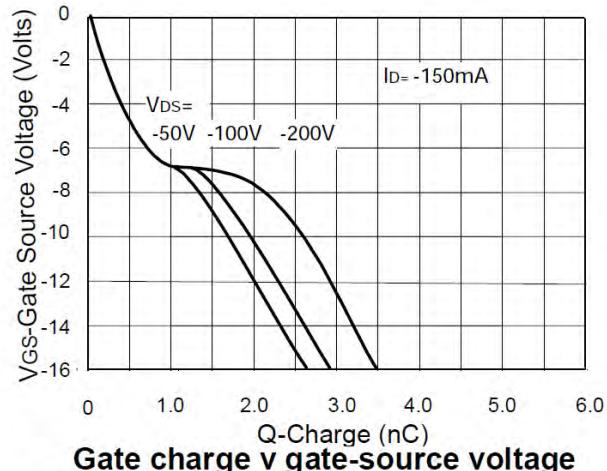


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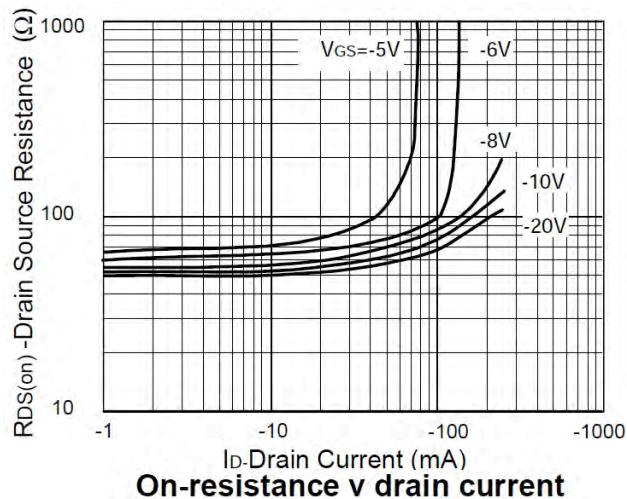
Electrical Characteristics (cont.)



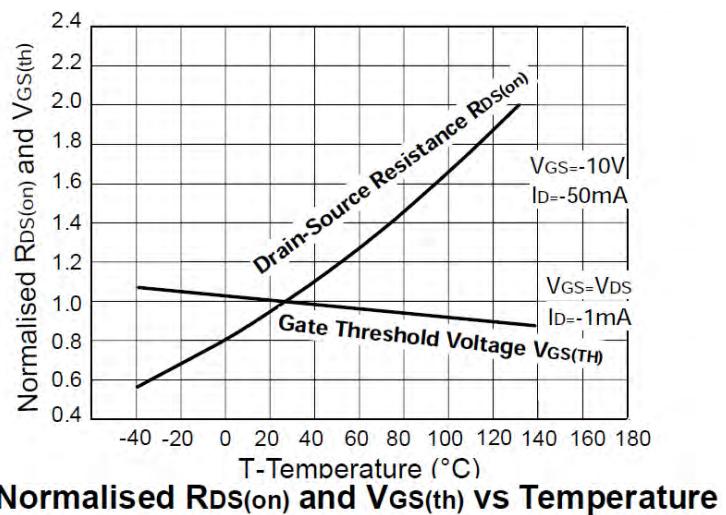
Transconductance v gate-source voltage



Gate charge v gate-source voltage



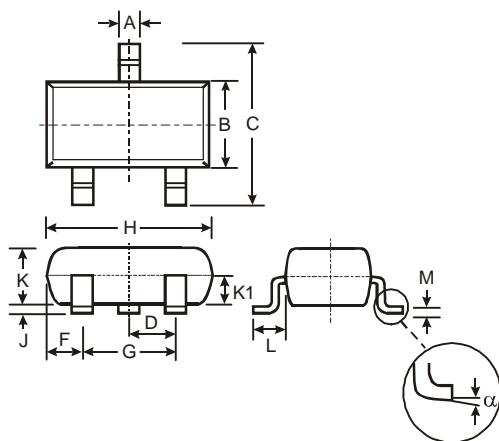
On-resistance v drain current



Normalised $R_{D(on)}$ and $V_{GS(th)}$ vs Temperature

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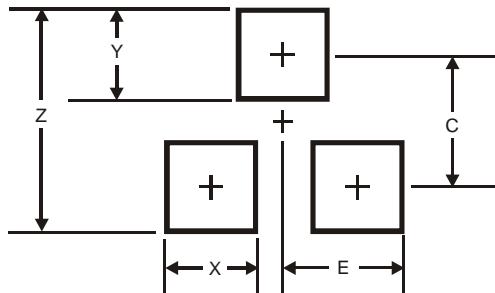
Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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